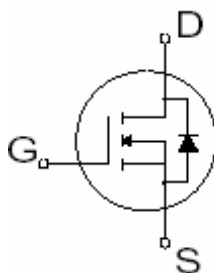


- Extremely high dv/dt capability
- Low Gate Charge Qg results in Simple Drive Requirement
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability



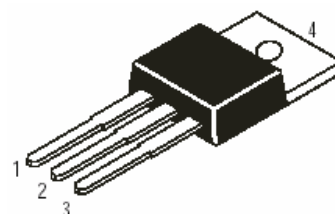
$$V_{DS} = 800V$$

$$I_{D25} = 3.0A$$

$$R_{DS(ON)} = 4.8 \Omega$$

## Description

StarMOS is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimises the JFET effect, increases packing density and reduces the on-resistance. StarMOS also achieves faster switching speeds through optimised gate layout with planar stripe DMOS technology.



Pin1-Gate  
Pin2-Drain  
Pin3-Source

## Application

- Switching application

## Absolute Maximum Ratings

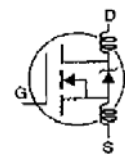
|                        | Parameter                                        | Max.                 | Units |
|------------------------|--------------------------------------------------|----------------------|-------|
| $I_D@T_C=25^{\circ}C$  | Continuous Drain Current, $V_{GS}@10V$           | 3                    | A     |
| $I_D@T_C=100^{\circ}C$ | Continuous Drain Current, $V_{GS}@10V$           | 1.9                  |       |
| $I_{DM}$               | Pulsed Drain Current ①                           | 12                   |       |
| $P_D@T_C=25^{\circ}C$  | Power Dissipation                                | 107                  | W     |
|                        | Linear Derating Factor                           | 0.85                 | W/°C  |
| $V_{GS}$               | Gate-to-Source Voltage                           | ±30                  | V     |
| $E_{AS}$               | Single Pulse Avalanche Energy ②                  | 320                  | mJ    |
| $I_{AR}$               | Avalanche Current ①                              | 3                    | A     |
| $E_{AR}$               | Repetitive Avalanche Energy ①                    | 10.7                 | mJ    |
| dv/dt                  | Peak Diode Recovery dv/dt ③                      | 4.5                  | V/ns  |
| $T_J$<br>$T_{STG}$     | Operating Junction and Storage Temperature Range | - 55 to +150         | °C    |
|                        | Soldering Temperature, for 10 seconds            | 300(1.6mm from case) |       |
|                        | Mounting Torque, 6-32 or M3 screw                | 10 lbf.in(1.1N.m)    |       |

## Thermal Resistance

|                 | Parameter                           | Min. | Typ. | Max. | Units |
|-----------------|-------------------------------------|------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-case                    | —    | —    | 1.17 | °C/W  |
| $R_{\theta CS}$ | Case-to-Sink, Flat, Greased Surface | —    | 0.5  | —    |       |
| $R_{\theta JA}$ | Junction-to-Ambient                 | —    | —    | 62.5 |       |

**Electrical Characteristics @T<sub>J</sub>=25 °C(unless otherwise specified)**

|                                        | Parameter                            | Min. | Typ. | Max. | Units | Test Conditions                                                               |
|----------------------------------------|--------------------------------------|------|------|------|-------|-------------------------------------------------------------------------------|
| V <sub>(BR)DSS</sub>                   | Drain-to-Source Breakdown Voltage    | 800  | —    | —    | V     | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA                                    |
| ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub> | Breakdown Voltage Temp.Coefficient   | —    | 1.0  | —    | V/°C  | Reference to 25°C, I <sub>D</sub> =250μA                                      |
| R <sub>DS(on)</sub>                    | Static Drain-to-Source On-resistance | —    | 4.0  | 4.8  | Ω     | V <sub>GS</sub> =10V, I <sub>D</sub> =1.5A ④                                  |
| V <sub>GS(th)</sub>                    | Gate Threshold Voltage               | 3.0  | —    | 5.0  | V     | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                      |
| g <sub>fs</sub>                        | Forward Transconductance             | —    | 3.0  | —    | S     | V <sub>DS</sub> =50V, I <sub>D</sub> =1.5A                                    |
| I <sub>DSS</sub>                       | Drain-to-Source Leakage current      | —    | —    | 10   | μA    | V <sub>DS</sub> =800V, V <sub>GS</sub> =0V                                    |
|                                        |                                      | —    | —    | 100  |       | V <sub>DS</sub> =640V, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C             |
| I <sub>GSS</sub>                       | Gate-to-Source Forward leakage       | —    | —    | 100  | nA    | V <sub>GS</sub> =30V                                                          |
|                                        | Gate-to-Source Reverse leakage       | —    | —    | -100 |       | V <sub>GS</sub> =-30V                                                         |
| Q <sub>g</sub>                         | Total Gate Charge                    | —    | 13   | 16.5 | nC    | I <sub>D</sub> =3A                                                            |
| Q <sub>gs</sub>                        | Gate-to-Source charge                | —    | 3.4  | —    |       | V <sub>DS</sub> =640V                                                         |
| Q <sub>gd</sub>                        | Gate-to-Drain("Miller") charge       | —    | 5.8  | —    |       | V <sub>GS</sub> =10V                                                          |
| t <sub>d(on)</sub>                     | Turn-on Delay Time                   | —    | 15   | 40   | nS    | V <sub>DD</sub> =400V                                                         |
| t <sub>r</sub>                         | Rise Time                            | —    | 43.5 | 95   |       | I <sub>D</sub> =3A                                                            |
| t <sub>d(off)</sub>                    | Turn-Off Delay Time                  | —    | 22.5 | 55   |       | R <sub>G</sub> =25Ω                                                           |
| t <sub>f</sub>                         | Fall Time                            | —    | 32   | 75   |       |                                                                               |
| L <sub>D</sub>                         | Internal Drain Inductance            | —    | 4.5  | —    | nH    | Between lead,<br>6mm(0.25in.)<br>from package<br>and center of<br>die contact |
| L <sub>S</sub>                         | Internal Source Inductance           | —    | 7.5  | —    |       |                                                                               |
| C <sub>iss</sub>                       | Input Capacitance                    | —    | 543  | 705  | pF    | V <sub>GS</sub> =0V                                                           |
| C <sub>oss</sub>                       | Output Capacitance                   | —    | 54   | 70   |       | V <sub>DS</sub> =25V                                                          |
| C <sub>rss</sub>                       | Reverse Transfer Capacitance         | —    | 5.5  | 7.5  |       | f=1.0MHz                                                                      |


**Source-Drain Ratings and Characteristics**

|                 | Parameter                                 | Min.                                                                                            | Typ. | Max. | Units | Test Conditions                                                         |
|-----------------|-------------------------------------------|-------------------------------------------------------------------------------------------------|------|------|-------|-------------------------------------------------------------------------|
| I <sub>S</sub>  | Continuous Source Current<br>(Body Diode) | —                                                                                               | —    | 3.0  | A     | MOSFET symbol<br>showing the<br>integral reverse<br>p-n junction diode. |
| I <sub>SM</sub> | Pulsed Source Current<br>(Body Diode) ①   | —                                                                                               | —    | 12   |       |                                                                         |
| V <sub>SD</sub> | Diode Forward Voltage                     | —                                                                                               | —    | 1.4  | V     | T <sub>J</sub> =25°C, I <sub>S</sub> =3.0A, V <sub>GS</sub> =0V ④       |
| t <sub>rr</sub> | Reverse Recovery Time                     | —                                                                                               | 642  | —    | nS    | T <sub>J</sub> =25°C, I <sub>F</sub> =3.0A                              |
| Q <sub>rr</sub> | Reverse Recovery Charge                   | —                                                                                               | 4.0  | —    | nC    | di/dt=100A/μs ④                                                         |
| t <sub>on</sub> | Forward Turn-on Time                      | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> + L <sub>D</sub> ) |      |      |       |                                                                         |

Notes:

① Repetitive rating;pulse width limited by  
max.junction temperature(see figure 11)

② L = 67mH, I<sub>AS</sub> = 3.0A, V<sub>DD</sub> = 50V,  
R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C

③ I<sub>SD</sub> ≤ 3.0A, di/dt ≤ 200A/μS, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 25°C

④ Pulse width ≤ 300 μS; duty cycle ≤ 2%